

# Superconducting diode effect

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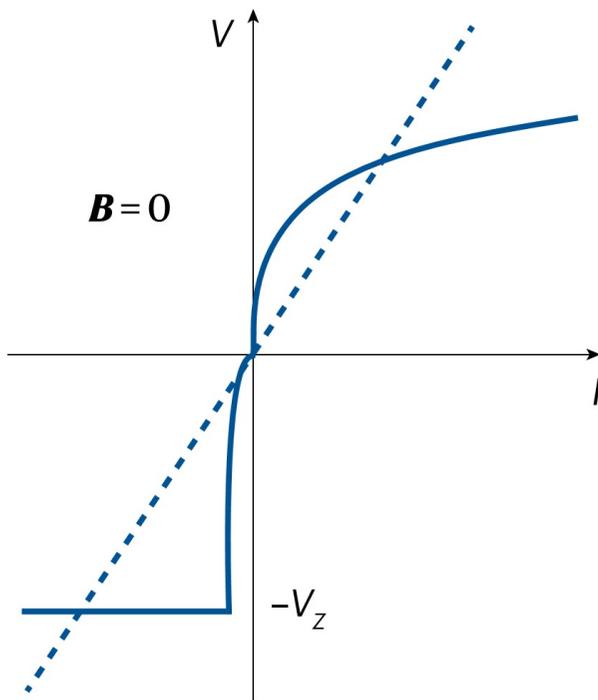


- [1a] Ya.V. Fominov, D.S. Mikhailov, *Asymmetric higher-harmonic SQUID as a Josephson diode*, Phys. Rev. B 106, 134514 (2022).
- [1b] **G.S. Seleznev**, Ya.V. Fominov, *Influence of capacitance and thermal fluctuations on the Josephson diode effect in asymmetric higher-harmonic SQUIDs*, Phys. Rev. B 110, 104508 (2024).
- [2] D.S. Kalashnikov, **G.S. Seleznev**, A. Kudriashov, Y. Babich, D.Yu. Vodolazov, Ya.V. Fominov, V.S. Stolyarov, *Diode effect in Shapiro steps in an asymmetric SQUID with a superconducting nanobridge*, accepted to Phys. Rev. B (2025).
- [3] **Yu.A. Dmitrievtsev**, Ya.V. Fominov, *Superconducting orbital diode effect in SN bilayers*, in preparation.

# Diode

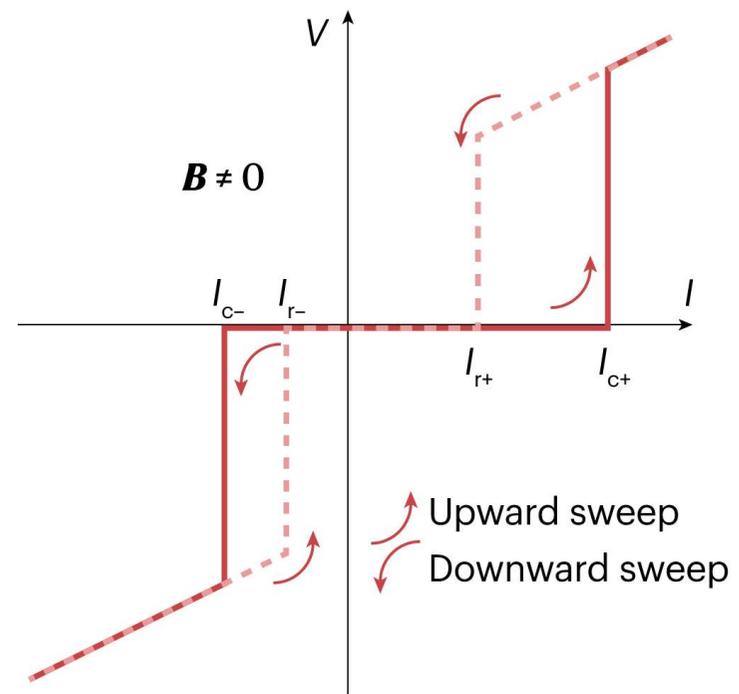
[from review Nadeem *et al.*, Nat. Rev. Phys. (2023)]

Normal



vs

Superconducting

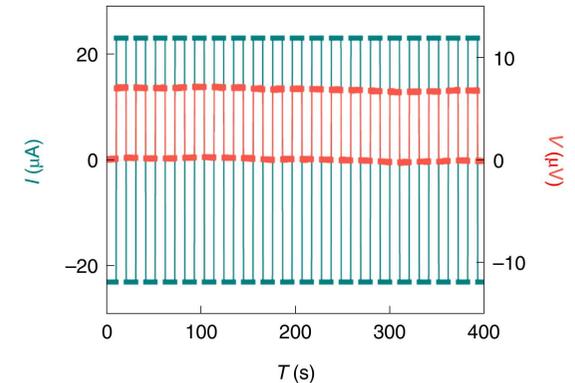


*Standard ingredients of the superconducting diode effect:*

- broken inversion symmetry (P-symmetry)
- broken time-reversal symmetry (T-symmetry)

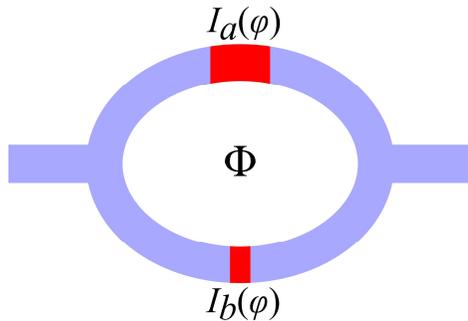
## Superconducting diode effect: Why so popular?

- Interesting fundamental effect depending on symmetries and, hence, probing them (e.g, diode effect at zero magnetic field  $\Rightarrow$  intrinsic TRSB)
- Possible applications:
  - voltage rectifiers
  - filters
  - current converters
- Diverse physical platforms and physical mechanisms:
  - bulk systems and Josephson junctions
    - vortices
    - stray fields of magnets
    - exchange field and spin-orbit coupling
    - topological materials
    - spatial symmetry breaking either on atomic level (NCS crystals) or macroscopically by heterostructure design
    - self-field effects in long Josephson junctions and in SQUIDs
    - SQUIDs with higher Josephson harmonics



Pal *et al.*, Nature Physics (2022)

## 1a. Josephson diode effect in asymmetric SQUIDs with higher harmonics



$$\varphi_a - \varphi_b = \phi, \quad \phi = 2\pi \frac{\Phi}{\Phi_0}$$

CRP of the SQUID:  $I_s(\varphi, \phi) = I_a(\varphi_a) + I_b(\varphi_b) = I_a(\varphi + \phi/2) + I_b(\varphi - \phi/2)$

Sinusoidal case:  $I_s(\varphi, \phi) = I_{a1} \sin(\varphi + \phi/2) + I_{b1} \sin(\varphi - \phi/2) = I_1(\phi) \sin(\varphi + \gamma)$

where  $I_1(\phi) = \sqrt{I_{a1}^2 + I_{b1}^2 + 2I_{a1}I_{b1} \cos \phi}$

$$\tan \gamma = \frac{I_{a1} - I_{b1}}{I_{a1} + I_{b1}} \tan \frac{\phi}{2}$$

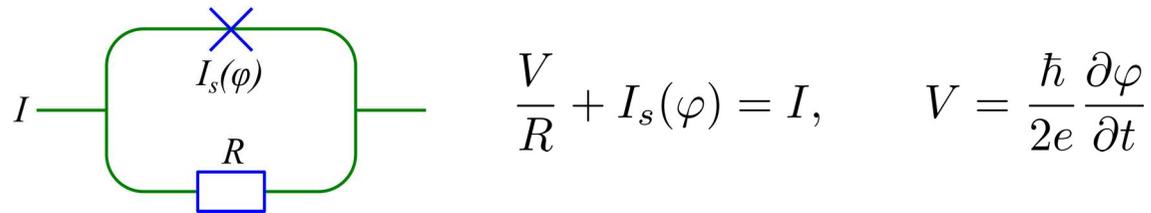
Critical currents in two directions:  $I_c^+ = I_c^-$

More generally, this is so

(a) in symmetric SQUIDs with arbitrary  $I_a(\varphi) = I_b(\varphi)$

(b) when  $I_a(\varphi)$  and  $I_b(\varphi)$  contain the same single harmonic (with arbitrary amplitudes)

## Resistively-shunted junction (RSJ) model



$I_s(\varphi) = I_1 \sin \varphi$  — sinusoidal current-phase relation (CPR)

Units:  $\omega_0 = 2eI_1R/\hbar, \quad \tau = \omega_0 t, \quad j = I/I_1, \quad v = V/I_1R$

Resistively-shunted junction (RSJ) model:  $v = \dot{\varphi}$   
 $\dot{\varphi} + \sin \varphi = j$

[Aslamazov, Larkin, Ovchinnikov (1968),  
Stewart (1968),  
McCumber (1968)]

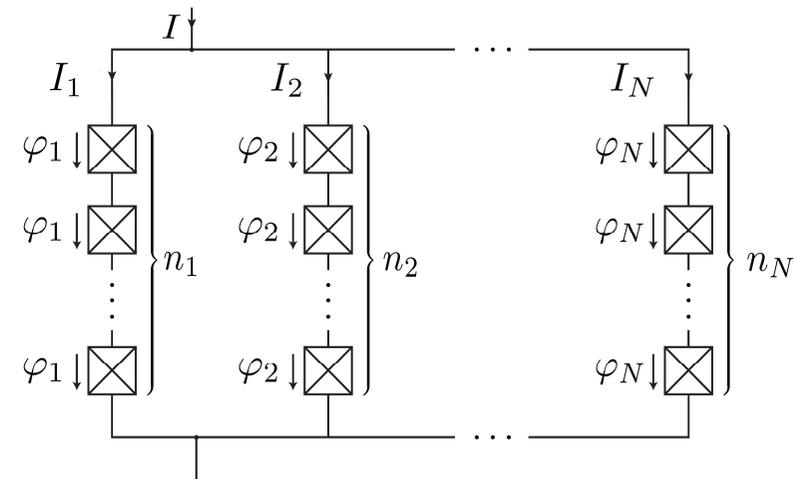
## Higher Josephson harmonics

$$I_s(\varphi) = \sum_{n=1}^{\infty} I_n \sin n\varphi \quad \text{— nonsinusoidal CPR with higher harmonics}$$

- higher orders wrt barrier transparency
- point contacts
- SNS junctions
- SFS junctions
- CPR engineering
- etc.

RSJ equation:  $\dot{\varphi} + J(\varphi) = j, \quad J(\varphi) = I_s(\varphi)/I_1$

[Haenel, Can, arXiv(2022)]



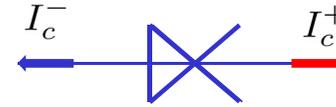
# Asymmetric higher-harmonic SQUID as a Josephson diode

General case:  $I_c^+ \neq I_c^-$

“Minimal model”:

$$I_a(\varphi) = I_{a1} \sin \varphi$$

$$I_b(\varphi) = I_{b1} \sin \varphi + I_{b2} \sin 2\varphi$$



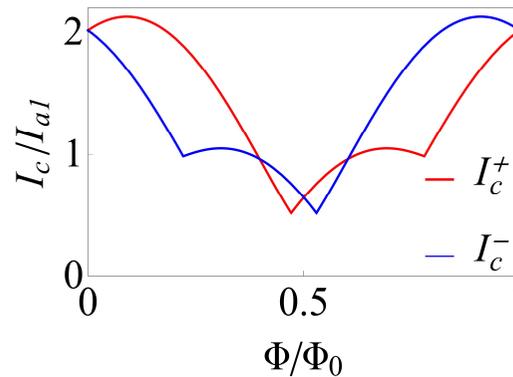
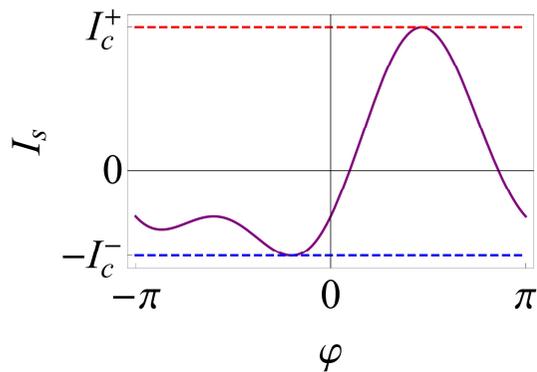
Effective Josephson junction with

$$J(\varphi) = \sin \varphi + A \sin(2\varphi - \tilde{\phi})$$

where

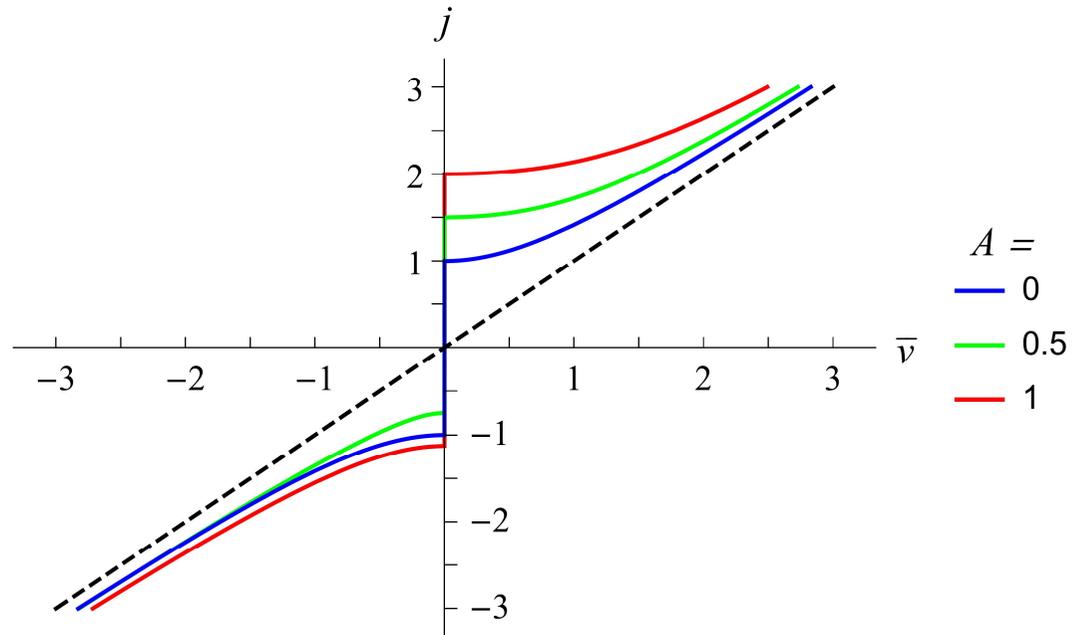
$$A(\phi) = I_{b2}/I_1(\phi), \quad \tilde{\phi} = \phi + 2\gamma(\phi)$$

Analytics in limiting cases: diode effect at  $A \sin \tilde{\phi} \neq 0$



— asymmetry of critical currents

## Asymmetry of the CVC

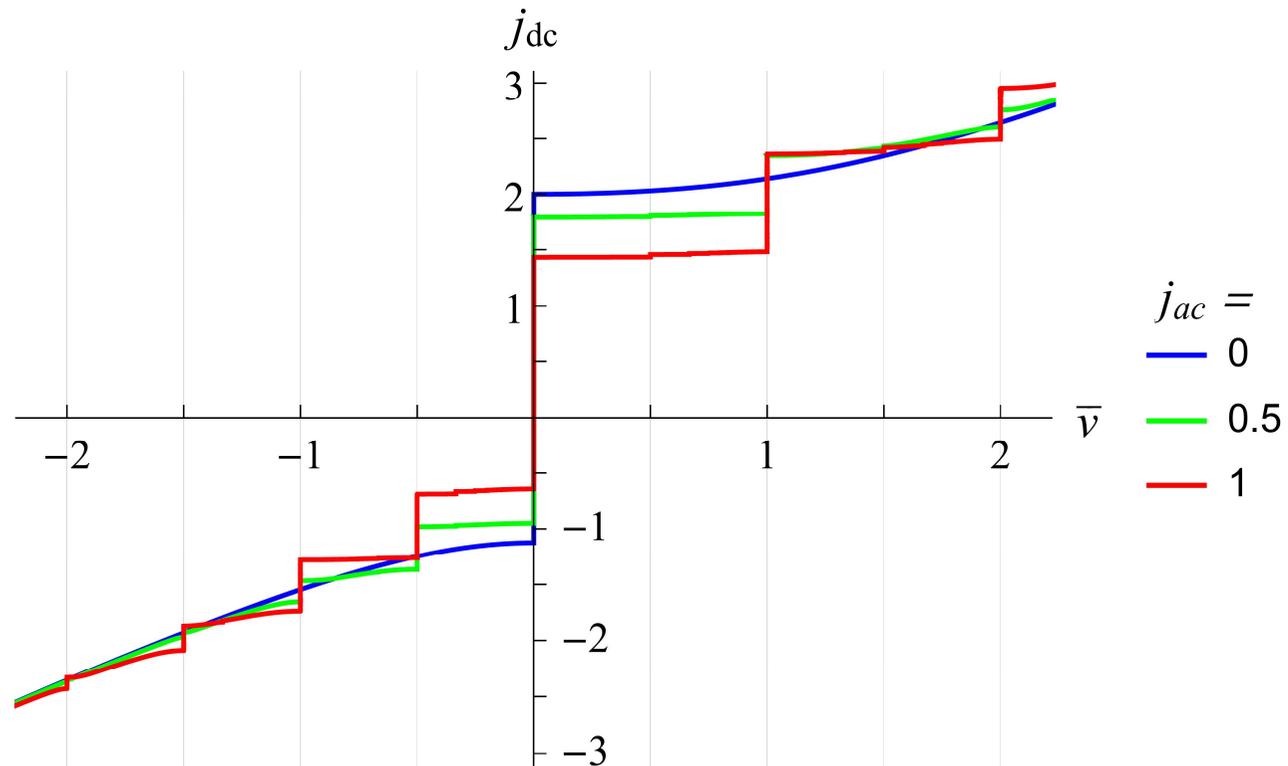


Diode effect:

$$j_c^+ \neq j_c^-$$
$$j(-\bar{v}) \neq -j(\bar{v})$$

## Asymmetry of the Shapiro steps

$$j = j_{dc} + j_{ac} \cos \omega t$$



Diode effect:  $j_c^+ \neq j_c^-$   
 $j_{dc}(-\bar{v}) \neq -j_{dc}(\bar{v})$

## Conclusions-1a

Josephson diode effect in asymmetric SQUIDs with higher Josephson harmonics.

Minimal model:  $J(\varphi) = \sin \varphi + A \sin(2\varphi - \tilde{\phi})$ , at  $A \sin \tilde{\phi} \neq 0$

- Asymmetric critical current:  $I_c^+ \neq I_c^-$
- Asymmetric current-voltage characteristic:  $I(-V) \neq -I(V)$
- Asymmetric integer and fractional Shapiro steps (current-driven regime),  
$$\bar{V} = \left(\frac{n}{k}\right) \frac{\hbar\omega}{2e}$$
- Efficiency and polarity of the diode effect depend on the external magnetic flux

[1a] Ya.V. Fominov, D.S. Mikhailov, *Asymmetric higher-harmonic SQUID as a Josephson diode*, Phys. Rev. B **106**, 134514 (2022).

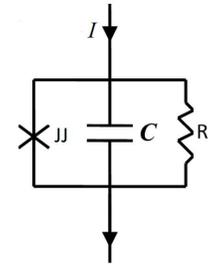
## 1b. Effects of capacitance and temperature

RSJ model  $\Rightarrow$  RCSJ model (added capacitance and thermal fluctuations):

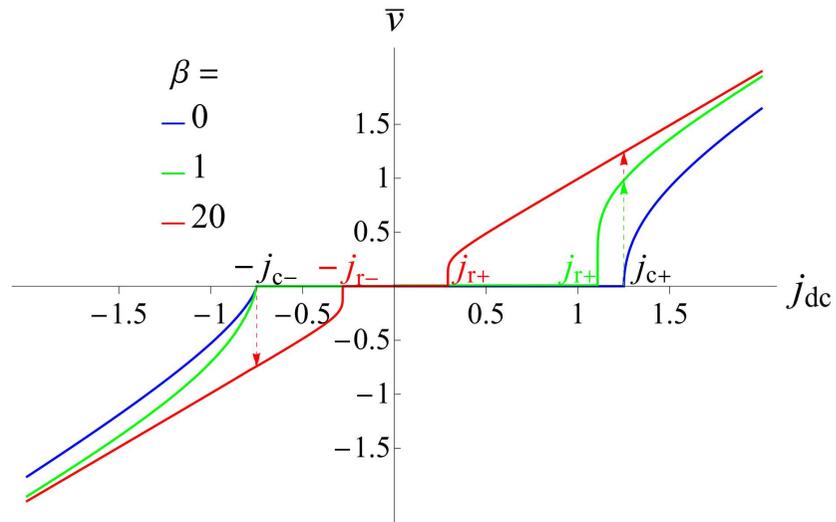
$$\frac{d^2\varphi}{d\tilde{\tau}^2} + \varepsilon \frac{d\varphi}{d\tilde{\tau}} + J(\varphi) = j_{\text{dc}} + j_{\text{ac}} \cos(\tilde{\omega}\tilde{\tau} + \delta) + \xi(\tilde{\tau})$$

$$\varepsilon = 1/\sqrt{\beta}, \quad \beta = (2e/\hbar)I_1R^2C, \quad \tilde{\tau} = \omega_p t, \quad \omega_p = \sqrt{2eI_1/\hbar C}$$

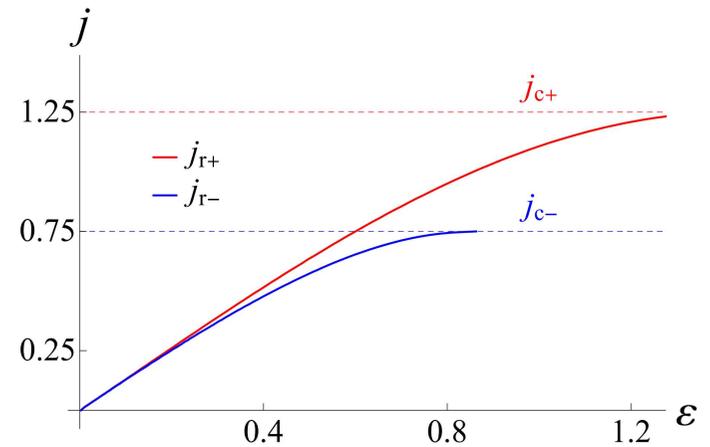
$\uparrow$   
McCumber parameter



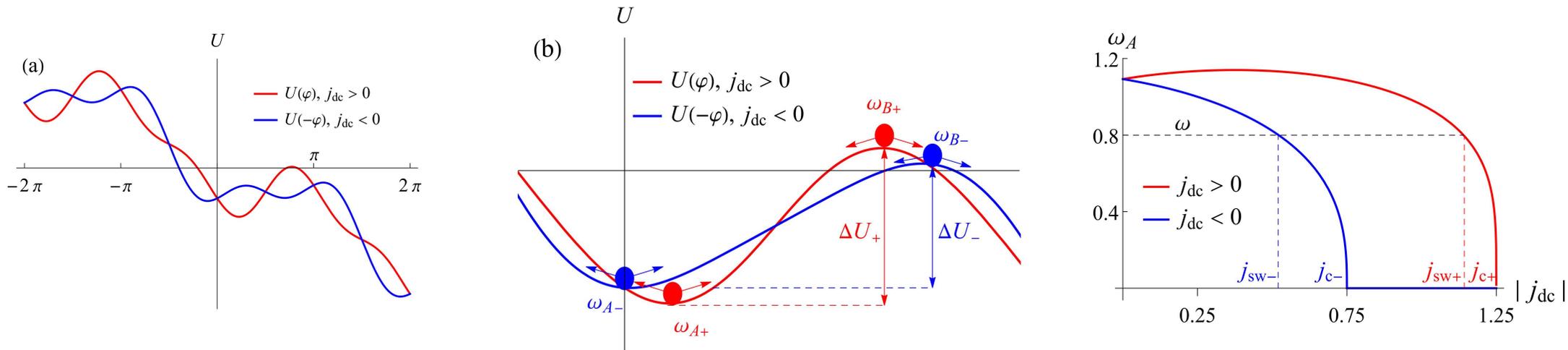
## Effects of capacitance



- Asymmetry in the R state is generally suppressed by capacitance (both without and with external ac irradiation)
- New effect: asymmetry of the retrapping currents  $j_{r\pm}$
- Single-sides hysteresis



## Asymmetry of the switching currents (S to R state)



- Effect of external ac irradiation on the S state:  
Josephson plasma resonances at  $\omega = \omega_{A\pm}(j_{sw\pm})$

$$j_{sw\pm} = \sqrt{1 - \tilde{\omega}^4} + \frac{2A\tilde{\omega}^6 \cos \tilde{\phi}}{\sqrt{1 - \tilde{\omega}^4}} \pm A(1 + 2\tilde{\omega}^4) \sin \tilde{\phi}$$

## Effects of thermal fluctuations

$$\beta\ddot{\phi} + \dot{\phi} + \sin\varphi + A \sin(2\varphi - \tilde{\phi}) = j_{\text{dc}} + \xi(\tau)$$

$$\langle \xi(\tau)\xi(\tau') \rangle = 2\theta\delta(\tau - \tau'), \text{ where } \theta = 2eT/\hbar I_1 = T/E_J$$

- Fokker-Planck equation for the distribution function in the low-temperature limit  $\theta \ll \Delta U_{\pm}$  (i.e., escape time  $\gg$  sliding time)

Generalization of:

[Stratonovich — Textbook (1961)]

[Ivanchenko, Zil'berman (1968)]

[Ambegaokar, Halperin (1969)]

Zero capacitance, asymmetric CVC:

$$\langle \bar{v}_{\pm}(j_{\text{dc}}) \rangle = \pm 2\omega_{A\pm}\omega_{B\pm} \sinh\left(\frac{j_{\text{dc}}\pi}{\theta}\right) \exp\left(\frac{-\Delta U_{\pm} - j_{\text{dc}}\pi}{\theta}\right)$$

Nonzero capacitance, asymmetric escape rates:

$$\tilde{\tau}_{l\pm}^{-1} = \frac{\tilde{\omega}_{\text{att}\pm}}{2\pi} \exp\left(-\frac{\Delta U_{\pm}}{\theta}\right)$$

## Effects of thermal fluctuations: switching currents

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Slowly increasing current:  $j_{\text{dc}}(\tilde{\tau}) = a\tilde{\tau}$ ,  $a\tilde{\tau}_{l\pm} \ll 1$

Switching: probability to remain in the potential well = 1/2

$$j_{\text{sw}\pm} = j_{c\pm} - \begin{cases} \left( \frac{\theta}{u_{c\pm}} \ln \frac{2\theta\omega_{c\pm}^2}{(6\pi \ln 2)\varepsilon a u_{c\pm}} \right)^{2/3}, & \varepsilon \gg 1 \\ \left( \frac{\theta}{u_{c\pm}} \ln \frac{2\theta\omega_{c\pm}}{(6\pi \ln 2) a u_{c\pm}} \right)^{2/3}, & \varepsilon \ll 1 \end{cases}$$

## Conclusions-1b

Capacitance:

- Generally, capacitance suppresses the diode effect in the R state

**At the same time, qualitatively new effects:**

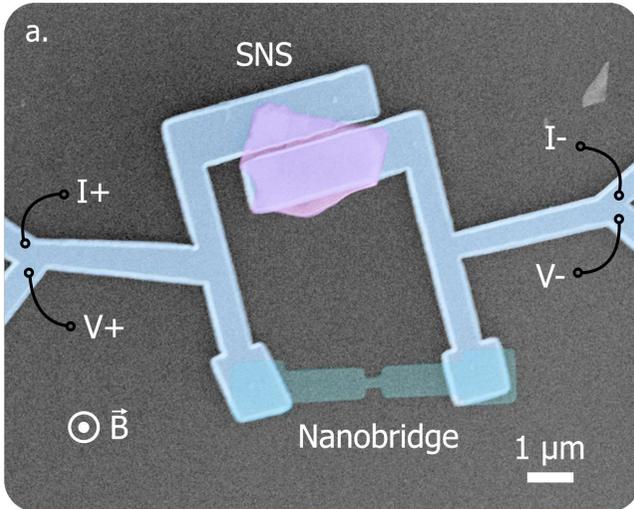
- Asymmetry of the retrapping currents
- Single-sided hysteresis
- Asymmetric switching currents due to the Josephson plasma resonances

Thermal fluctuations:

- Exponentially asymmetric CVC below the critical currents
- Asymmetry of the thermal switching currents

[1b] **G.S. Seleznev**, Ya.V. Fominov, *Influence of capacitance and thermal fluctuations on the Josephson diode effect in asymmetric higher-harmonic SQUIDs*, Phys. Rev. B **110**, 104508 (2024).

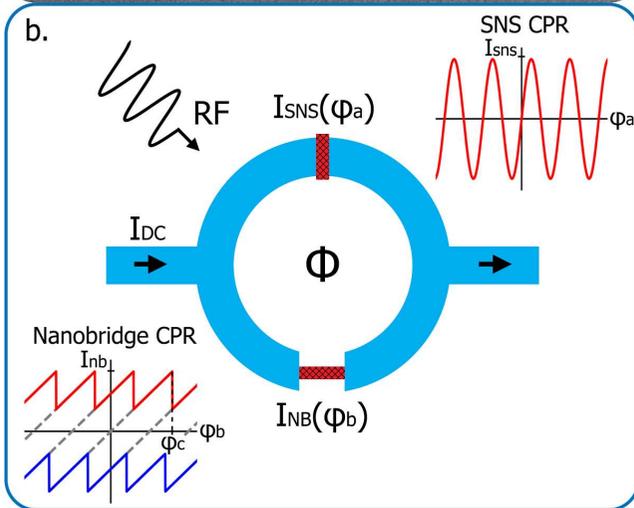
## 2. Diode effect in Shapiro steps in an asymmetric SQUID with a superconducting nanobridge



CPR of the SQUID with nanobridge:

$$I_s(\varphi) = I_{\text{SNS}}(\phi) \sin(\varphi + \phi) + I_{\text{NB}}(\varphi)$$

$$\frac{I_s(\varphi)}{I_{\text{nb}}} = A_{0\pm} + \sum_{k=1}^{\infty} A_{k\pm} \sin(k(\varphi + \delta_{k\pm}))$$

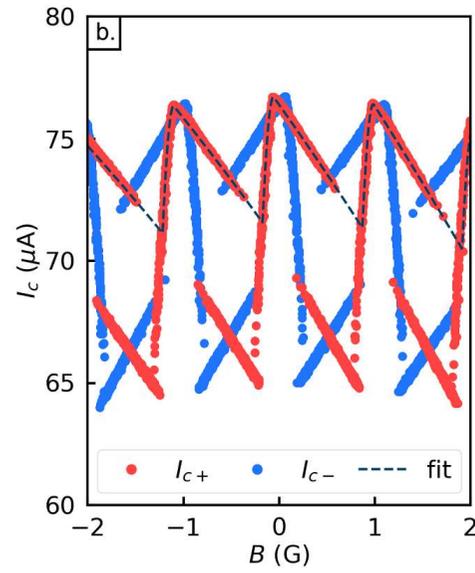
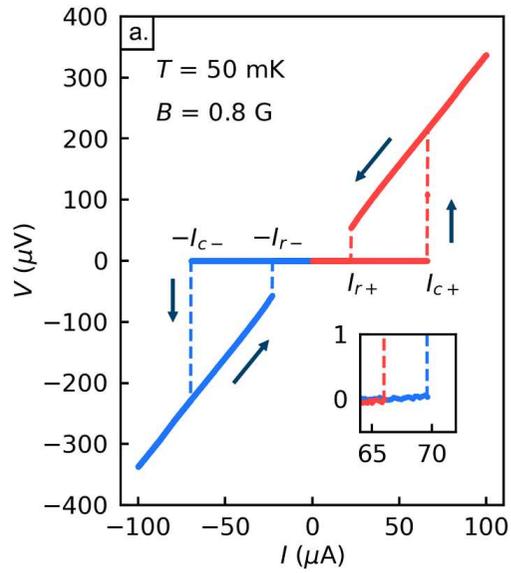


Asymmetry of the first Josephson harmonic at  $\sin \varphi_c \sin \phi \neq 0$ :

$$A_{1\pm} = \sqrt{\left(\frac{I_{\text{SNS}}(\phi)}{I_{\text{nb}}}\right)^2 + \frac{4}{\varphi_c^2} - \frac{4I_{\text{SNS}}(\phi)}{I_{\text{nb}}\varphi_c} \cos(\phi \pm \varphi_c)}$$

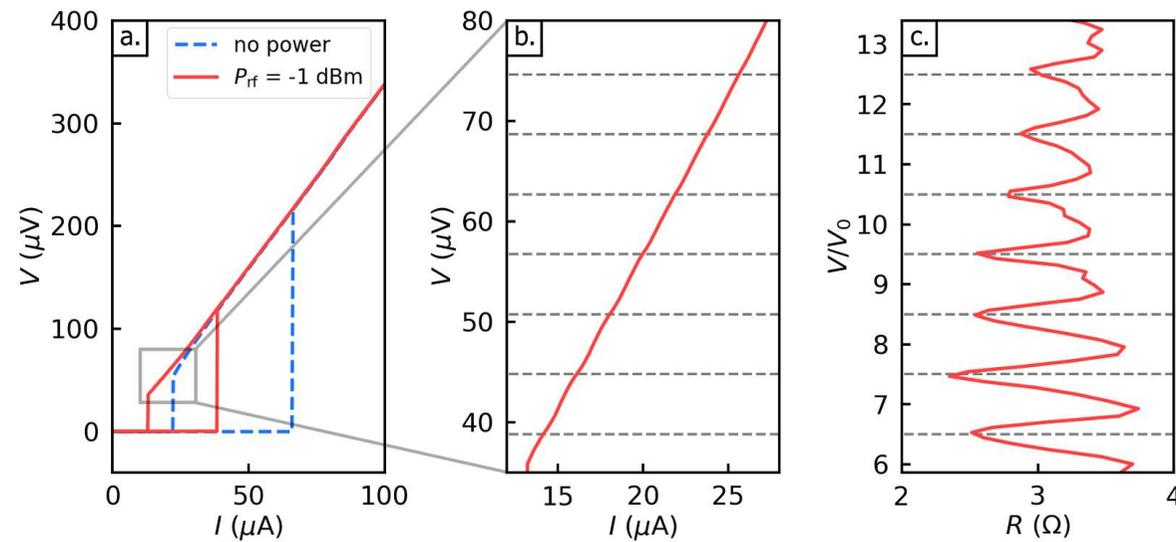
— leads to JDE!

## dc and ac measurements

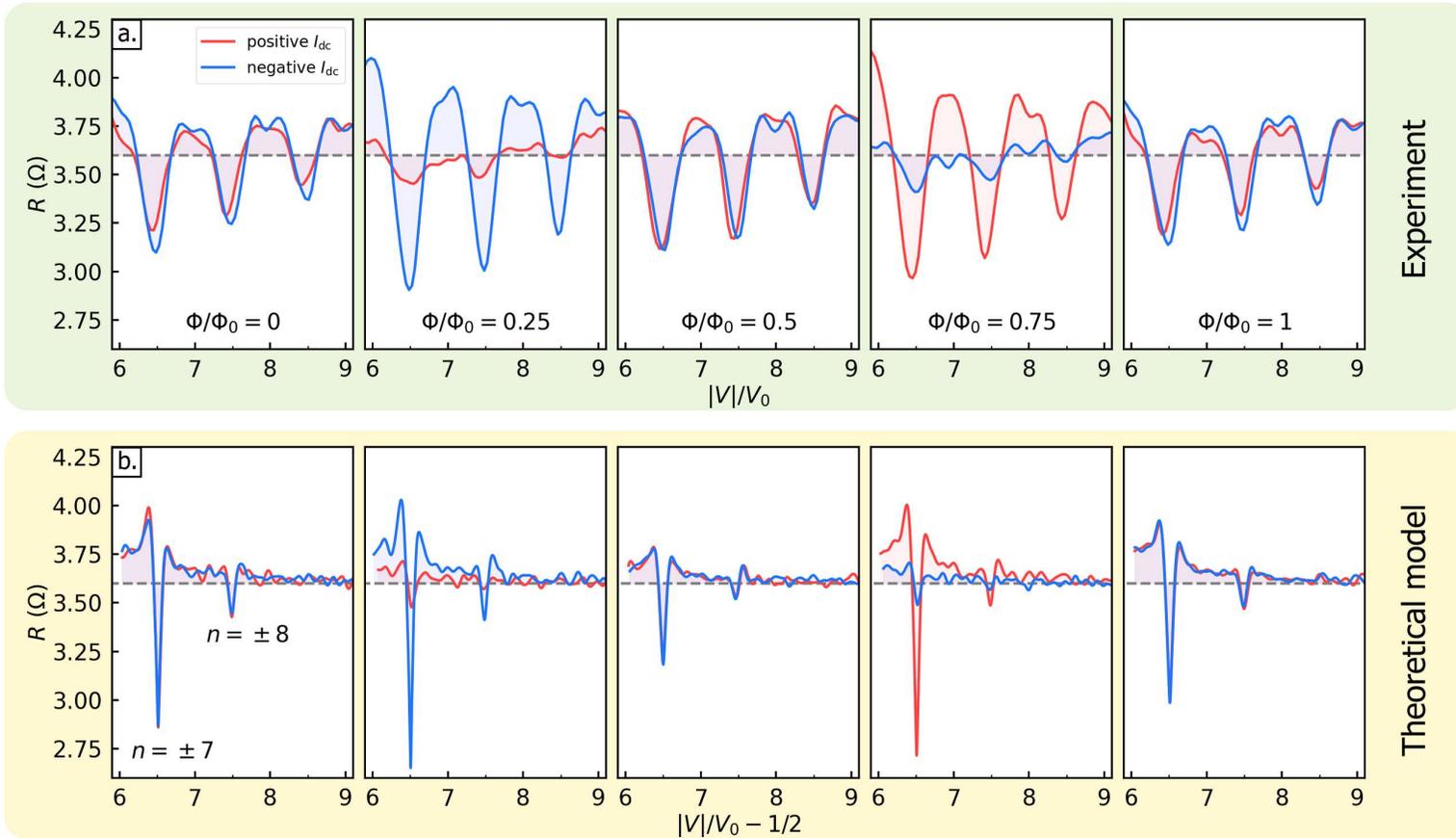


— dc measurements: asymmetry of the critical currents

— ac measurements: Shapiro steps



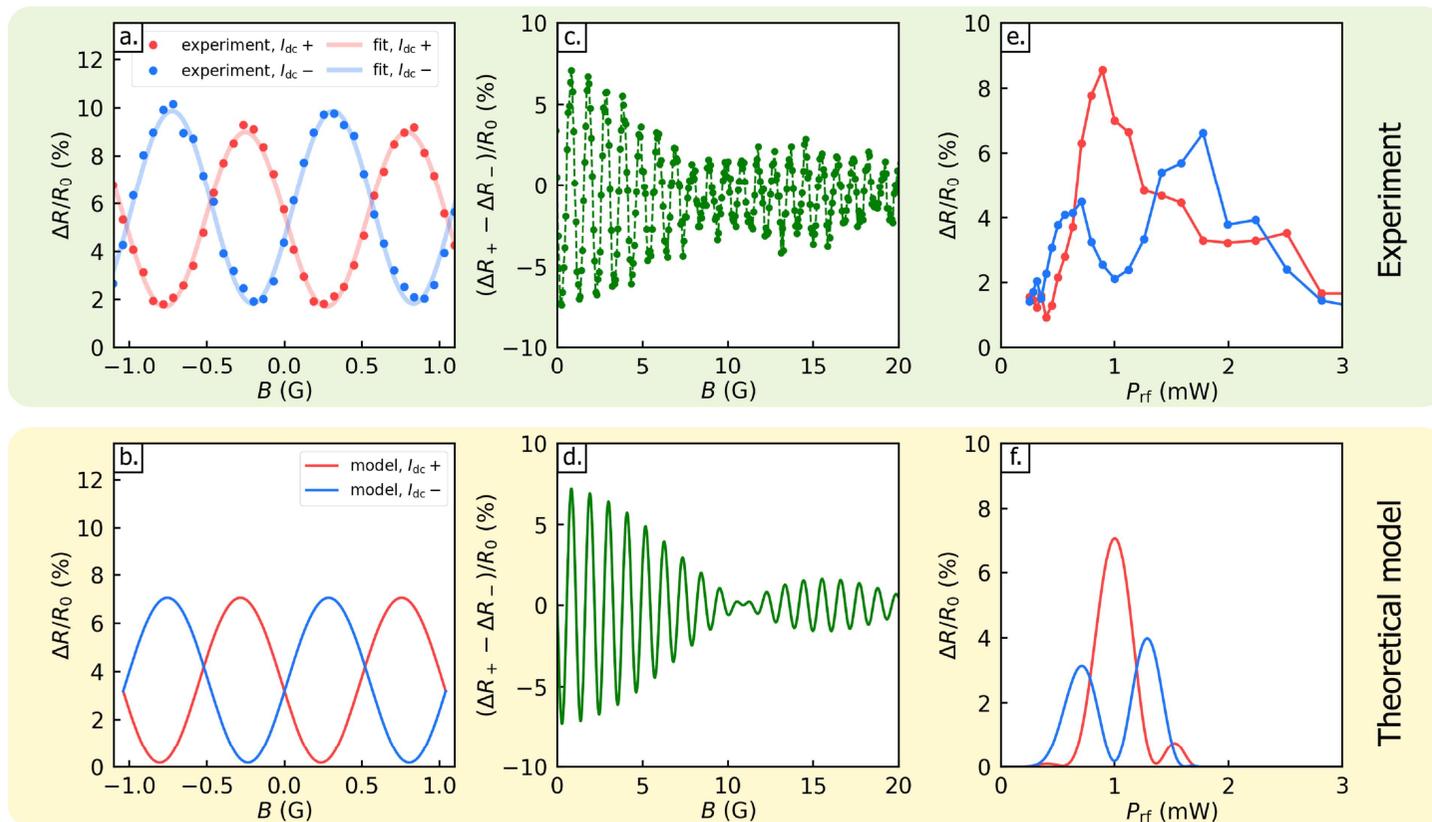
## Asymmetry of Shapiro steps



Theory: RSJ model with thermal noise:  $\langle \xi(\tau)\xi(\tau') \rangle = 2\mathcal{T}\delta(\tau - \tau')$

↪  $\mathcal{T} = 2eT/\hbar I_{nb}$

## Analysis of the Shapiro steps



$$\mathcal{T}_{\pm} = \mathcal{T} / A_{1\pm} J_n(j_{ac}/\omega)$$

Theory: single-harmonic CPR.

Analytics at the centers of the Shapiro steps:

$$\frac{R_{\pm}}{R_0} = I_0^{-2} (1/\mathcal{T}_{\pm}) = \begin{cases} (2\pi/\mathcal{T}_{\pm}) \exp(-2/\mathcal{T}_{\pm}), & \mathcal{T}_{\pm} \ll 1 \\ (1 - 1/2\mathcal{T}_{\pm}^2), & \mathcal{T}_{\pm} \gg 1 \end{cases}$$

Dependence on power of microwave irradiation: account of energy balance.

## Conclusions-2

Asymmetric SQUID with nanobridge:

- Josephson diode effect manifestations in the critical currents and Shapiro steps
- New mechanism: asymmetry of the first Josephson harmonic in the effective SQUID's CPR due to (linear) multivalued CPR of the nanobridge:

$$A_{1+} \neq A_{1-} \text{ at } \sin \varphi_c \neq 0$$

[2] D.S. Kalashnikov, **G.S. Seleznev**, A. Kudriashov, Y. Babich, D.Yu. Vodolazov, Ya.V. Fominov, V.S. Stolyarov, *Diode effect in Shapiro steps in an asymmetric SQUID with a superconducting nanobridge*, accepted to Phys. Rev. B (2025).

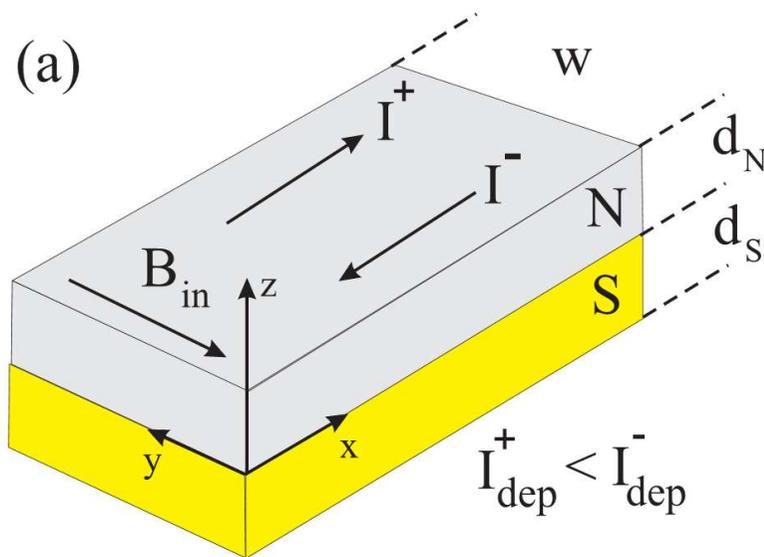
### 3. Superconducting orbital diode effect in SN bilayers

PHYSICAL REVIEW B **108**, 094517 (2023)

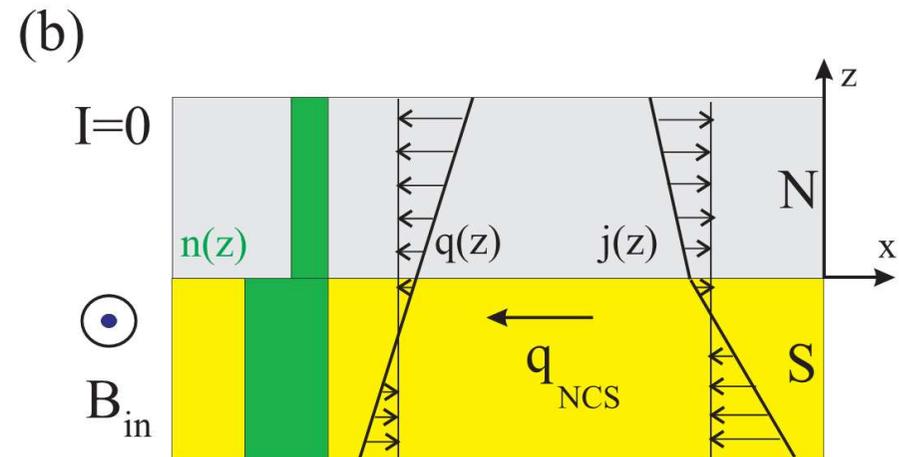
#### Finite momentum superconductivity in superconducting hybrids: Orbital mechanism

M. Yu. Levichev , I. Yu. Pashenkin , N. S. Gusev, and D. Yu. Vodolazov \*

*Institute for Physics of Microstructures, Russian Academy of Sciences, 603950 Nizhny Novgorod, GSP-105, Russia*



Symmetry-breaking vector:  $[\nabla n \times \mathbf{B}]$



Numerics in the case of transparent interface + experiment

## Analytics + interface effect

Analytics: dirty-limit theory (Usadel equations) in the case of weak inhomogeneity, development of

PHYSICAL REVIEW B, VOLUME 63, 094518 (2001)

**Superconductive properties of thin dirty superconductor-normal-metal bilayers**

Ya. V. Fominov and M. V. Feigel'man

Weakly inhomogeneous case:

1. Thin bilayer  $d \ll \xi$  + arbitrary interface transparency
2. Thick bilayer  $d \geq \xi$  + opaque interface

Condition: 
$$\frac{d^2}{\xi^2} \ll \max \left( 1, \frac{R}{R_0} \right)$$

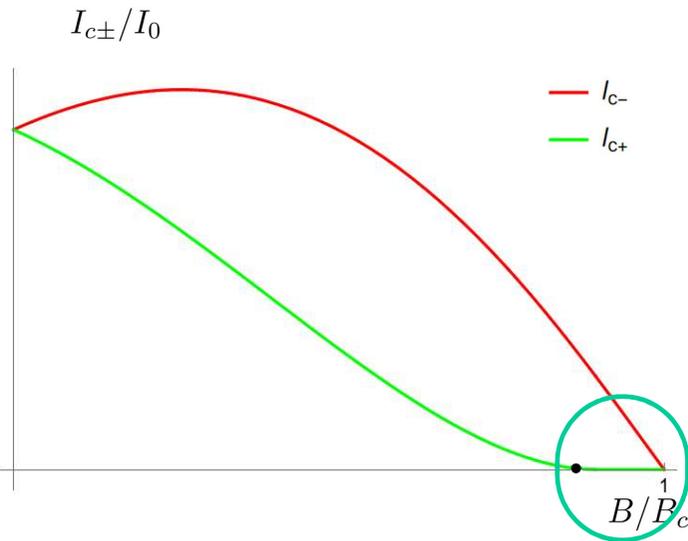
$$R_0 = R_q \frac{\delta_S + \delta_N}{|\Delta|}$$

$R$  — interface resistance

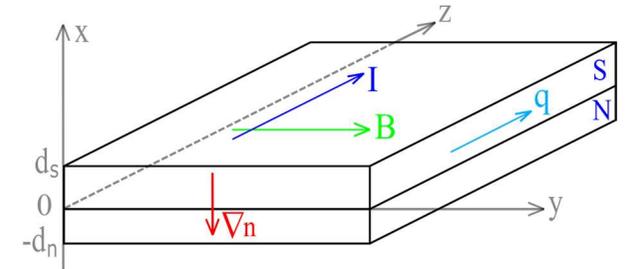
$R_q$  — quantum resistance

$\delta_{S,N} = (\nu_{S,N} V_{S,N})^{-1}$  — level spacing

# Supercurrent



$$\frac{I(q, B)}{I_0} = \frac{n_{\text{eff}}(q, B)}{n_0} \frac{q}{q_c} + k \left| \frac{\Delta(q, B)}{\Delta_0} \right|^2 \frac{B}{B_c}$$



— full diode effect is achievable

$n_0, \Delta_0$  — superfluid density and order parameter at  $T = 0$  and  $B = 0$

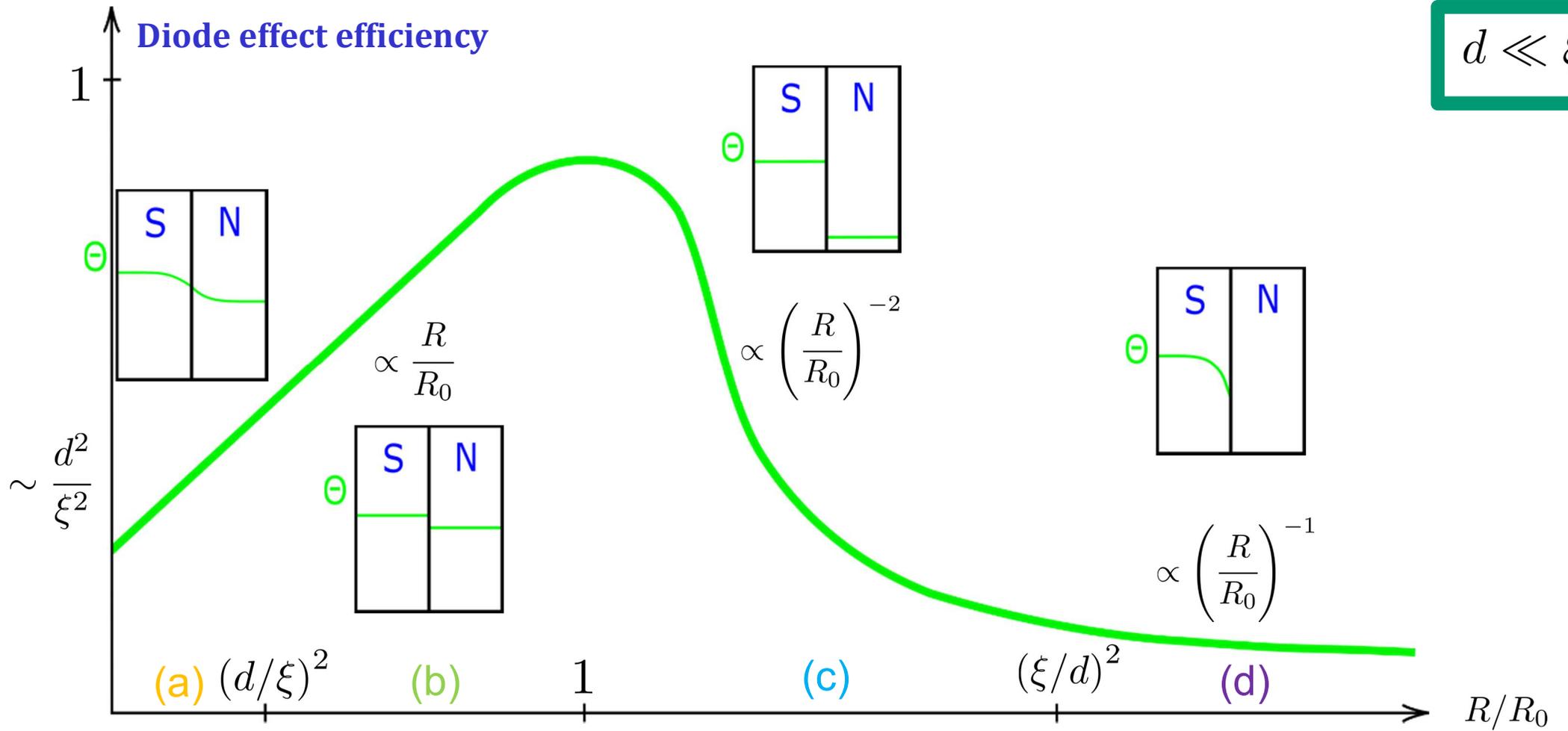
$q_c, B_c$  — critical momentum and magnetic field

$I_0$  — characteristic current value (at  $n_{\text{eff}} = n_0, q = q_c, B = 0$ )

$k \ll 1$  — parameter of weak inhomogeneity

## Interface effect: thin bilayer

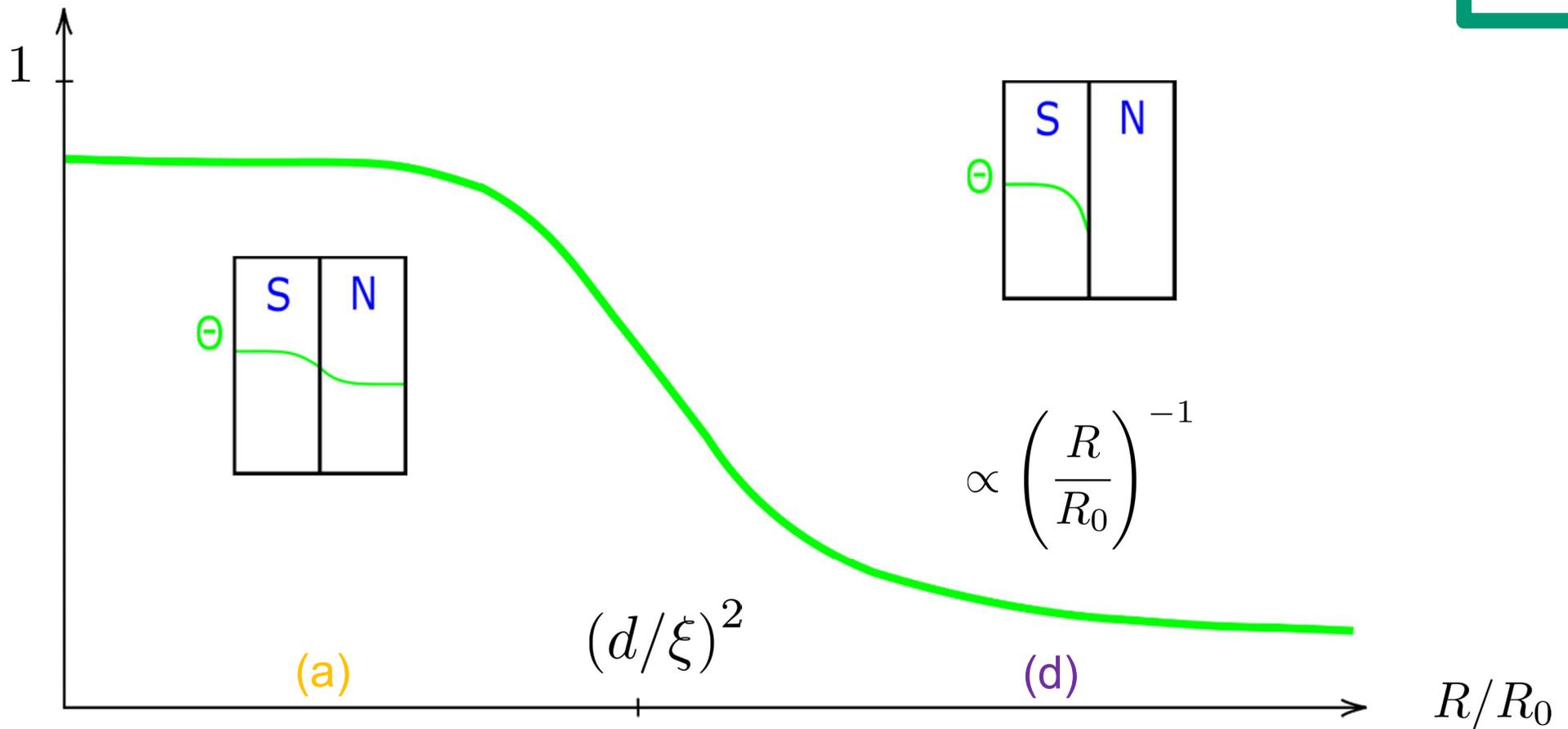
$d \ll \xi$



## Interface effect: thick bilayer

$$d \geq \xi$$

Diode effect efficiency



## Conclusions-3

Orbital diode effect in SN bilayers:

- Analytics in weakly inhomogeneous cases  $d^2/\xi^2 \ll \max(1, R/R_0)$
- Dependence of critical currents and diode efficiency on magnetic field: absolute visibility at  $B \rightarrow B_c$
- Effect of transparency: nonmonotonic diode efficiency in the limit of  $d \ll \xi$  with maximum at  $R \sim R_0$

Poster *Tu-3* today!

**Yuriy Dmitrievtsev**, Ya.V. Fominov, *Superconducting orbital diode effect in SN bilayers.*

## Conclusions

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Superconducting diode effect:

- Fundamental effect revealing symmetries of the system
- Diverse physical platforms and physical mechanisms

□ Work supported by the Russian Science Foundation (Grant No. 24-12-00357)